

50 V, 3 A PNP low VCEsat transistor

16 May 2022

**Product data sheet** 

### 1. General description

PNP low V<sub>CEsat</sub> transistor in a SOT89 plastic package.

NPN complement: PBSS4350X

### 2. Features and benefits

- SOT89 (SC-62) package
- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability: I<sub>C</sub> and I<sub>CM</sub>
- Higher efficiency leading to less heat generation
- Reduced printed-circuit board requirements
- AEC-Q101 qualified

### 3. Applications

- Power management
  - DC/DC converters
  - Supply line switching
  - Battery charger
  - LCD backlighting
- Peripheral drivers
  - Driver in low supply voltage applications (e.g. lamps and LEDs)
  - · Inductive load driver (e.g. relays, buzzers and motors)

### 4. Quick reference data

Table 1. Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	-50	V
I <sub>C</sub>	collector current			-	-	-3	A
I <sub>CM</sub>	peak collector current	limited by T <sub>j(max)</sub>		-	-	-5	A
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -2 A; $I_B$ = -200 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C		-	90	135	mΩ

# nexperia

### 5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter		С
2	С	collector		
3	В	base		B
			SOT89	sym132

### 6. Ordering information

Table 3. Ordering information							
Type number	Package	age					
	Name	Description	Version				
PBSS5350X	SOT89	plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body	<u>SOT89</u>				

### 7. Marking

Table 4. Marking codes	
Type number	Marking code
PBSS5350X	S46

### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-50	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-50	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-5	V
I <sub>C</sub>	collector current			-	-3	А
I <sub>CM</sub>	peak collector current	limited by T <sub>j(max)</sub>		-	-5	А
I <sub>B</sub>	base current			-	-0.5	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	550	mW
			[2]	-	1	W
			[3]	-	1.4	W
			[4]	-	1.6	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

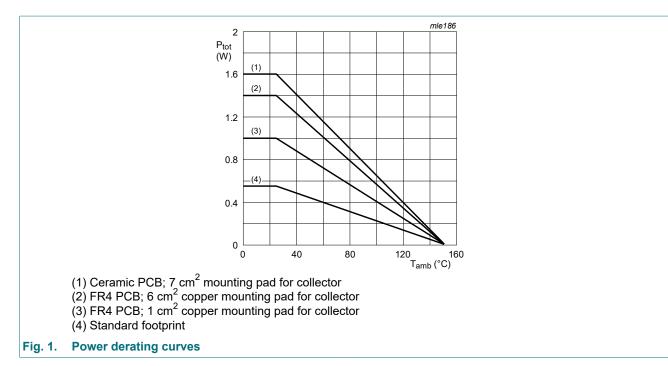
Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint. [1]

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup> [2]

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>. Device mounted on a ceramic printed-circuit board 7 cm<sup>2</sup>, single-sided copper, tin-plated. [3]

[4]

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### 9. Thermal characteristics

Table 6. The	rmal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air [1] [2] [3] [4]	[1]	-	-	225	K/W
			[2]	-	-	125	K/W
			[3]	-	-	90	K/W
			[4]	-	-	80	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	16	K/W

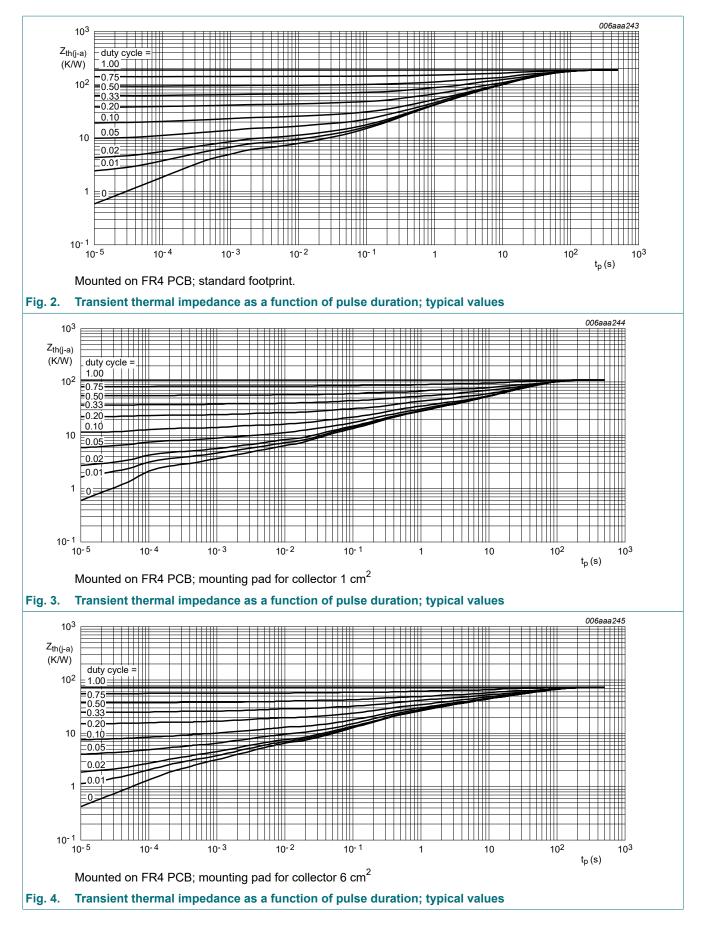
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

[4] Device mounted on a ceramic printed-circuit board 7 cm<sup>2</sup>, single-sided copper, tin-plated.

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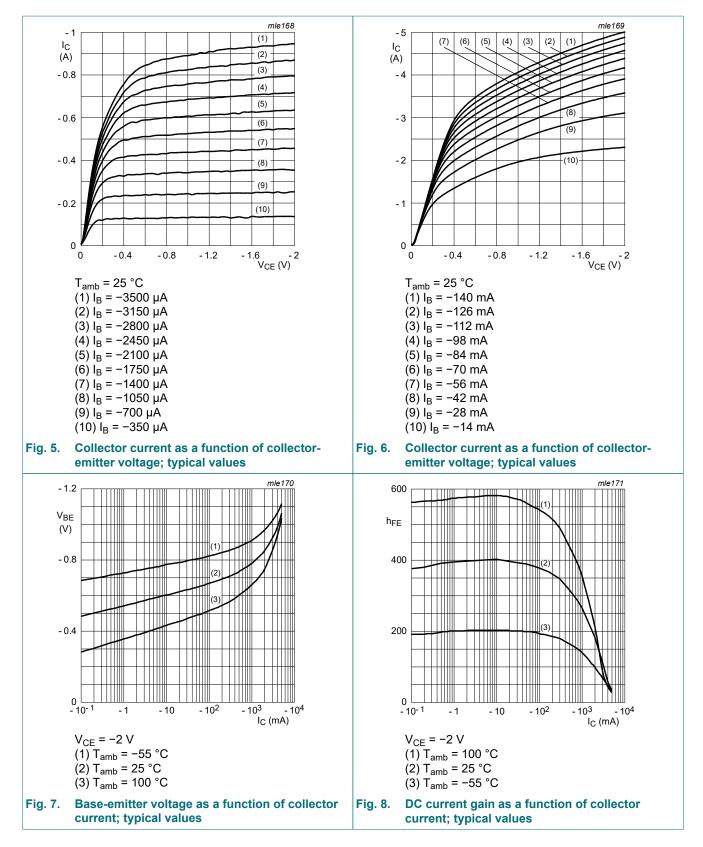


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# **10. Characteristics**

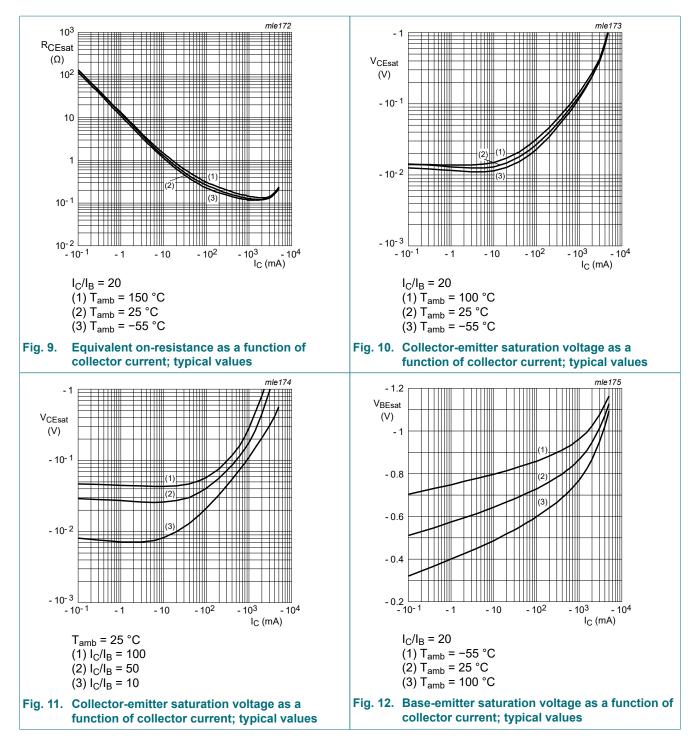
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V <sub>(BR)CBO</sub>	collector-base breakdown voltage	I <sub>C</sub> = -100 μA; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-50	-	-	V
V <sub>(BR)CEO</sub>	collector-emitter breakdown voltage	$I_{C}$ = -10 mA; $I_{B}$ = 0 A; $T_{amb}$ = 25 °C	-50	-	-	V
V <sub>(BR)EBO</sub>	emitter-base breakdown voltage (collector open)	I <sub>E</sub> = -100 μA; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-5	-	-	V
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = -50 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
	current	V <sub>CB</sub> = -50 V; I <sub>E</sub> = 0 A; T <sub>i</sub> = 150 °C	-	-	-50	μA
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE}$ = -50 V; $V_{BE}$ = 0 V; $T_{amb}$ = 25 °C	-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB}$ = -5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$ \begin{array}{l} V_{CE} = -2 \; V; \; I_C = 0.1 \; A; \; single \; pulse; \; t_p \leq \\ 300 \; \mu s; \; \delta \leq \; 0.02; \; T_{amb} = 25 \; ^\circ C \end{array} $	200	-	-	
		V <sub>CE</sub> = -2 V; I <sub>C</sub> = -0.5 A; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	200	-	-	
		$V_{CE}$ = -2 V; I <sub>C</sub> = -1 A; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	200	-	450	
		$V_{CE}$ = -2 V; I <sub>C</sub> = -2 A; pulsed; t <sub>p</sub> ≤ 300 µs; $\delta$ ≤ 0.02; T <sub>amb</sub> = 25 °C	130	-	-	
		V <sub>CE</sub> = -2 V; I <sub>C</sub> = -3 A; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	80	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = -0.5 A; I <sub>B</sub> = -50 mA; T <sub>amb</sub> = 25 °C	-	-	-90	mV
		I <sub>C</sub> = -1 A; I <sub>B</sub> = -50 mA; T <sub>amb</sub> = 25 °C	-	-	-180	mV
		I <sub>C</sub> = -2 A; I <sub>B</sub> = -100 mA; T <sub>amb</sub> = 25 °C	-	-	-320	mV
		I <sub>C</sub> = -2 A; I <sub>B</sub> = -200 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-	-270	mV
		I <sub>C</sub> = -3 A; I <sub>B</sub> = -300 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-	-390	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	I <sub>C</sub> = -2 A; I <sub>B</sub> = -200 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	90	135	mΩ
V <sub>BEsat</sub>	base-emitter saturation	I <sub>C</sub> = -2 A; I <sub>B</sub> = -100 mA; T <sub>amb</sub> = 25 °C	-	-	-1.1	V
	voltage	I <sub>C</sub> = -3 A; I <sub>B</sub> = -300 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-	-1.2	V
V <sub>BEon</sub>	base-emitter turn-on voltage	$V_{CE}$ = -2 V; I <sub>C</sub> = -1 A; T <sub>amb</sub> = 25 °C	-	-	-1.1	V
fT	transition frequency	V <sub>CE</sub> = -5 V; I <sub>C</sub> = -100 mA; f = 100 MHz; T <sub>amb</sub> = 25 °C	100	-	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	-	35	pF

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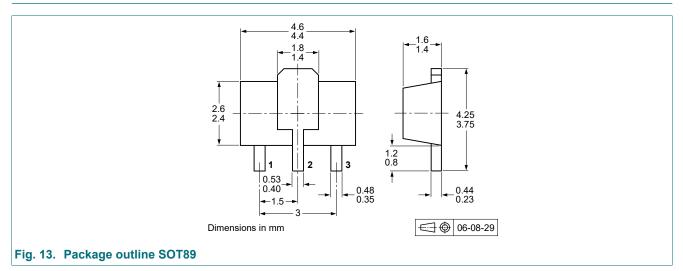
### **11. Test information**

#### **Quality information**

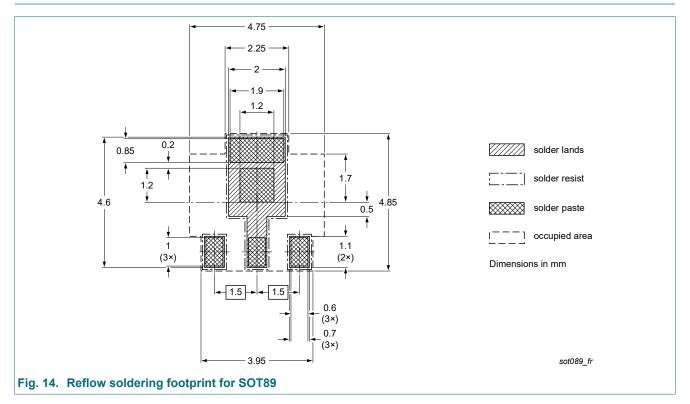
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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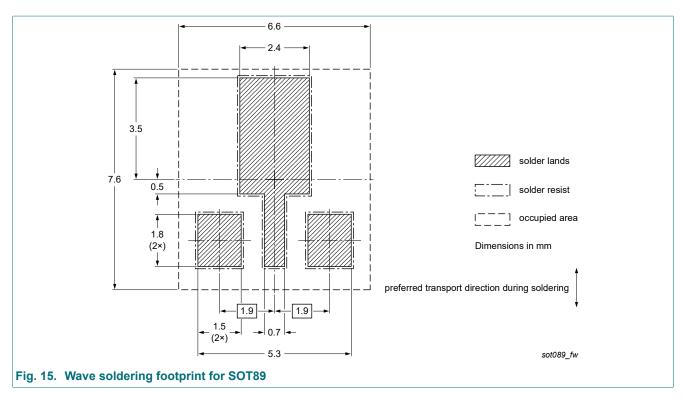
# 12. Package outline



### 13. Soldering



#### 50 V, 3 A PNP low VCEsat transistor



# 14. Revision history

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Release date	Data sheet status	Change notice	Supersedes			
20220516	Product data sheet	-	PBSS5350X v.2			
<ul> <li>The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia.</li> <li>Legal texts have been adapted to the new company name where appropriate.</li> </ul>						
20041104	Product data sheet	-	PBSS5350X v.1			
20031121	Product data sheet	-	-			
	<ul> <li>Release date</li> <li>20220516</li> <li>The format of this da Nexperia.</li> <li>Legal texts have bee</li> <li>20041104</li> </ul>	Release date     Data sheet status       20220516     Product data sheet       • The format of this data sheet has been redesin Nexperia.       • Legal texts have been adapted to the new con 20041104	Release date       Data sheet status       Change notice         20220516       Product data sheet       -         • The format of this data sheet has been redesigned to comply with the in Nexperia.       -         • Legal texts have been adapted to the new company name where approxed to the			

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#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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